L1: (1810) (memory near3 (flash cell device)) with ("STI" shallow adj trench isolation near3
L2: (1731) 1 and (etch$3 pattern$3)
L3: (1498) 2 and ((oxide insulat$3 dielectric conduct$ electrode metal) near3 gate)
L4: (1250) 3 and ((etch$3 pattern$3) with mask$3)
L5: (251) 4 and (stack with gate)
L6: (167) 5 and floating
L7: (159) 6 and isolat$3

Browse   Queue

DBs   0 ☑ Plurals
Default operat ☑ Highlight all hit terms initially

6 and isolat$3

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
13	☐	☐	US 20030137001 A1	20030724	13	Low voltage programmable and erasable Flash EEPROM	257/314	257/315
14	☐	☐	US 20030134474 A1	20030717	13	Low voltage programmable and erasable flash EEPROM	438/257	
15	☐	☐	US 20030122181 A1	20030703	19	Contactless nor-type memory array and its fabrication Methods	257/315	257/202; 257/205
16	☐	☐	US 20030122178 A1	20030703	7	Method for fabricating a flash memory having a T-shaped floating g	257/314	257/E29.129; 438/197
17	☐	☐	US 20030068860 A1	20030410	14	NON-VOLATILE MEMORY CELLS WITH SELECTIVELY FOR	438/257	
18	☐	☐	US 20030064563 A1	20030403	12	Flash memory and method of forming flash memory	438/257	438/264
19	☐	☐	US 20030030087 A1	20030213	19	Semiconductor memory device	257/296	
20	☐	☐	US 20030027390 A1	20030206	12	Methods of forming FLASH memories	438/257	438/296
21	☐	☐	US 20030022500 A1	20030130	14	Alternative related to SAS in flash EEPROM	438/692	
22	☐	☐	US 20030013250 A1	20030116	9	Nonvolatile memory device and manufacturing method thereof	438/201	257/E21.55
23	☐	☐	US 20030011025 A1	20030116	46	Nonvolatile semiconductor memory device and manufacturing method the	257/316	257/E21.682; 257/E27.103

EAST - [5049aa.wsp:1]

File View Edit Tools Window Help

L1: (1810) (memory near3 (flash cell device)) with ("STI" shallow adj trench isolation near3
L2: (1731) 1 and (etch$3 pattern$3)
L3: (1498) 2 and ((oxide insulat$3 dielectric conduct$ electrode metal) near3 gate)
L4: (1250) 3 and ((etch$3 pattern$3) with mask$3)
L5: (251) 4 and (stack with gate)
L6: (167) 5 and floating
L7: (159) 6 and isolat$3

Browse Queue

DBs   Plurals
Default operat Highlight all hit terms initially

6 and isolat$3

	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1			US 20030232472 A1	20031218	26	Methods of fabbricating a stack-gate non-volatile memory device and its c	438/257	
2			US 20030230783 A1	20031218	17	Integrated memory circuit and method of forming an integrated mem	257/390	257/208; 257/211;
3			US 20030224572 A1	20031204	7	Flash memory structure having a T-shaped floating gate and its fabricat	438/257	438/296; 438/593
4			US 20030203571 A1	20031030	14	Non-volatile memory cells with selectively formed floating gate	438/257	
5			US 20030199149 A1	20031023	17	Shallow trench isolation method and method for manufacturing non-volatil	438/424	
6			US 20030193064 A1	20031016	24	Self-aligned multi-bit flash memory cell and its contactless flash memory	257/315	
7			US 20030156460 A1	20030821	24	Self-aligned split-gate flash memory cell and its contactless memory array	365/185.33	365/185.18
8			US 20030155599 A1	20030821	15	Twin-cell flash memory structure and method	257/296	
9			US 20030146465 A1	20030807	20	SCALABLE MULTI-BIT FLASH MEMORY CELL AND ITS MEMO	257/314	257/315
10			US 20030143790 A1	20030731	25	Methods of fabricating a stack-gate flash memory array	438/197	
11			US 20030141541 A1	20030731	26	Dual-bit flash memory cells for forming high-density memory arrays	257/319	

Start | Inbox | [01] 0. | http:/ | Docu | eDA | EAS... | http:/ | 3:17 PM